

/ Descriptions

WR0585 ММ Ё QSQ æ Ñ ç s ll 1 Silicon NPN transistor in a TO-252 Plastic Package.

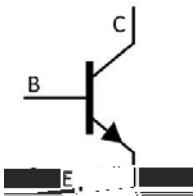
/ Features

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Complementary pair with 2SB649AD.

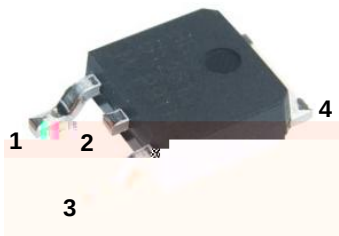
/ Applications

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Low frequency power amplifier.

/ Equivalent Circuit



/ Pinning



PIN1 χ Base PIN 2,4 χ Collector PIN 3 χ Emitter

/ h_{FE} Classifications & Marking

h _{FE} Classifications Symbol	B	C	D
h _{FE} Range	60 120	100 200	160 320

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	180	V
Collector to Emitter Voltage	V_{CEO}	160	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	1.5	A
Collector Current – Continuous(Pulse)	I_{CP}	3.0	A
Collector Power Dissipation	P_C	1.0	W
Collector Power Dissipation	$P_C(T_c=25^\circ C)$	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=1.0mA$ $I_E=0$	180			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=10mA$ $R_{BE}=\infty$	160			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=10mA$ $I_C=0$	5.0			V

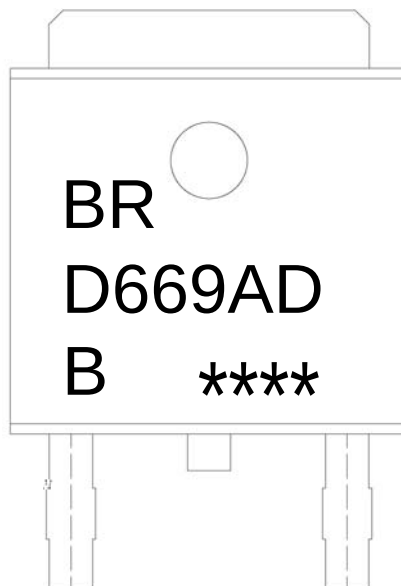
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



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Note:

BR:

D669AD:

B:

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Company Code

Product Type.

h_{FE} Classifications Symbol

Lot No. Code, code change with Lot No.

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